

/ Descriptions

SOT-89 PNP Silicon PNP transistor in a SOT-89 Plastic Package.

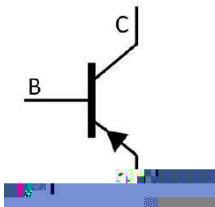
/ Features

2SD1898
High breakdown voltage, good h_{FE} linearity, low $V_{CE(sat)}$, complements the 2SD1898.

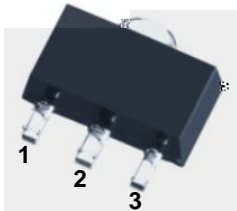
/ Applications

General power amplifier applications.

/ Equivalent Circuit



/ Pinning



PIN1 Base PIN 2 Collector PIN 3 Emitter

/ Marking

h_{FE} Classifications Symbol	P	Q	R
h_{FE} Range	82 180	120 270	180 390
Marking	HBHP*	HBHQ*	HBHR*

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-80	V
Collector to Emitter Voltage	V_{CEO}	-80	V
Emitter to Base Voltage	V_{EBO}	-5.0	V
Collector Current-Continuous	I_C	-1.0	A
Collector Current-Continuous(Pulse)	$*I_{CP}$	-2.0	A
Collector Power Dissipation	$**P_C$	0.5	W
	$*P_C$	2.0	W
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

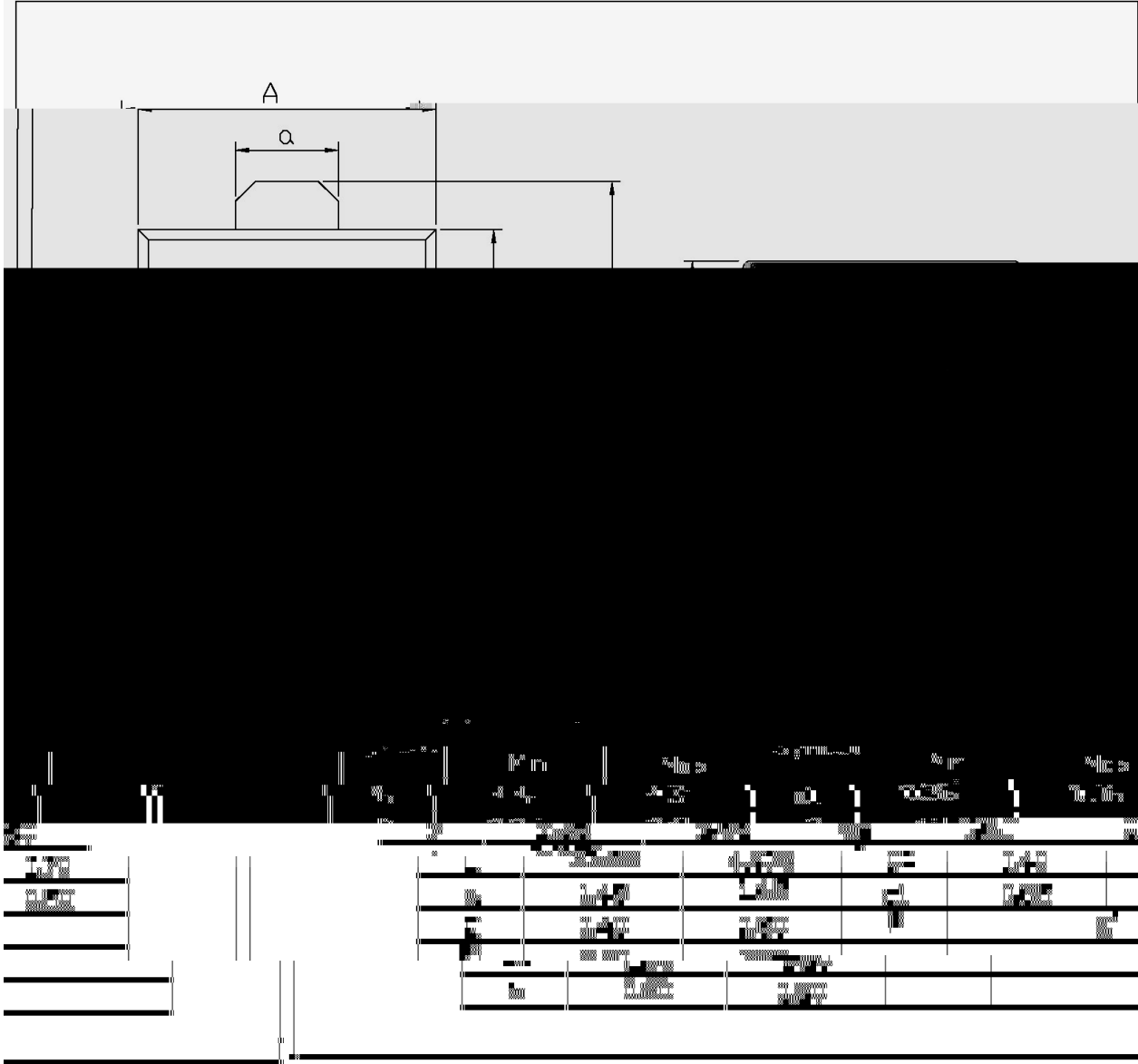
*Single pulse $P_w=100ms$ 100ms
 **mounted on 40x40x0.7mm ceramic board 40x40x0.7m

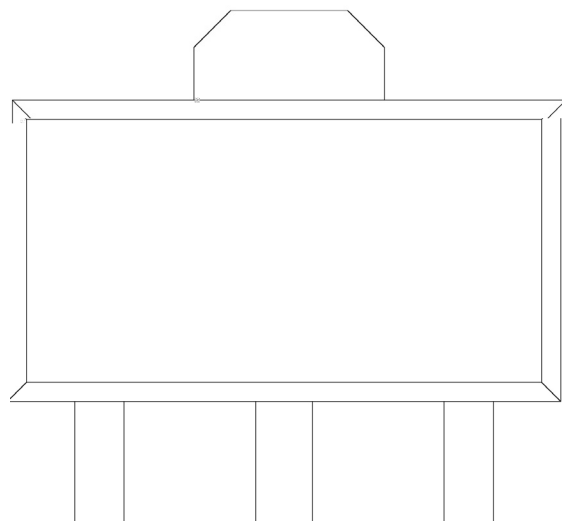
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Base Breakdown Voltage	V_{CBO}	I_C				

/ Package Dimensions

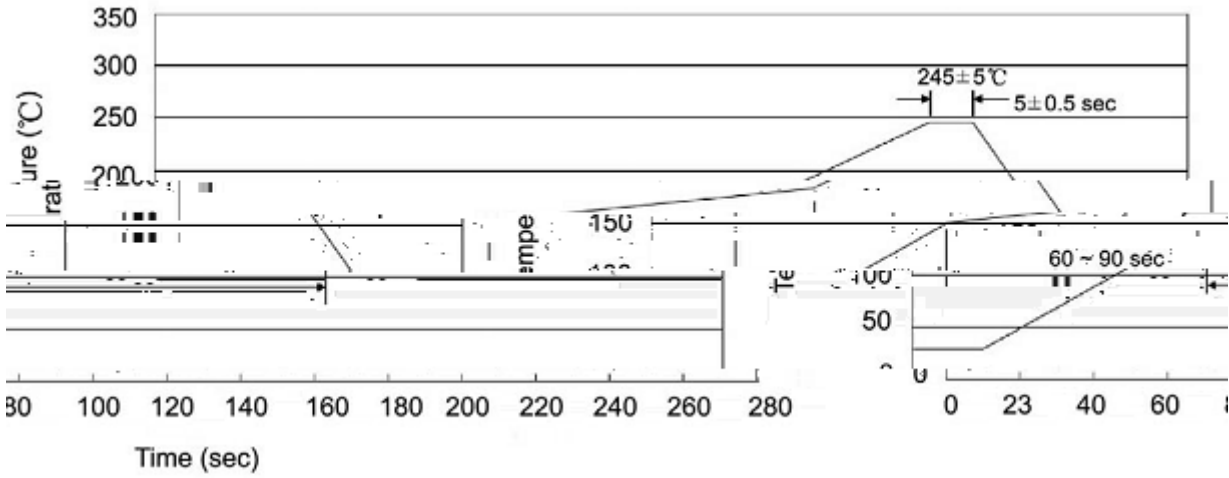
SOT-89

单位: mm





() / K\d g\iXk i\`Gif]`Δ`]fi`@`I`]\fn`Jfd` \i`e`^ZGY\$=i\`ž



Note:

- | | | | | | |
|---|-------|-----|-------|--------|---|
| 1 | 25 | 150 | 60 | 90sec; | 1.Preheating:25~150 , Time:60~90sec. |
| 2 | 245±5 | | 5±0.5 | sec; | 2.Peak Temp.:245±5 , Duration:5±0.5sec. |
| 3 | | 2 | 10 | /sec. | 3. Cooling Speed: 2~10 /sec. |

/ Resistance to Soldering Heat Test Conditions

260±5 10±1 sec. Temp.:260±5 Time:10±1 sec

/ Packaging SPEC.

/ REEL

Package Type	Units					Dimension (unit mm ³)		
	Units/Reel	Reels/Inner Box	Units/Inner Box	Inner Boxes/Outer Box	Units/Outer Box	Reel	Inner Box	Outer Box
SOT-89	1,000	7	7,000	8	56,000	7 ×12		